WHAT IS CLAIMED IS:

- 1. A display device comprising:
 - a substrate having an insulating surface;
 - a plurality of pixel electrodes formed over said substrate;
- a plurality of first n-channel thin film transistors for switching said pixel electrodes;
- a driver circuit formed over said substrate for switching said first thin film transistors, said driver circuit comprising a plurality of said second thin film transistors,

wherein all of said second thin film transistors are n-channel thin film transistors.

- 2. The display device according to claim 1 wherein said display device is a liquid crystal device.
- 3. The display device according to claim 1 further comprising another driver circuit comprising IC chips for driving said first thin film transistors.
 - 4. A display device comprising:
 - a substrate having an insulating surface;
- a plurality of first lines extending in a first direction over said substrate;
- a plurality of second lines extending across said first lines over said substrate;
- a plurality of pixels defined by said first lines and said second lines;
 - a plurality of pixel electrodes provided at said pixels;
- a plurality of switching elements provided at said pixels, each of said switching elements comprising at least one first thin film transistor;
 - a driver circuit formed over said substrate and

electrically connected to said plurality of first lines, said driver circuit comprising a plurality of second thin film transistors, each of said first and second thin film transistors comprising:

a semiconductor film formed over said substrate having at least source, drain and channel regions;

a gate insulating film formed on said semiconductor film; and

a gate electrode over said channel region with the gate insulating film interposed therebetween,

- 5. The display device according to claim 4 wherein said display device is a liquid crystal device.
- 6. The display device according to claim 4 further comprising another driver circuit comprising IC chips electrically connected to said plurality of second lines.
 - 7. A display device comprising:
 - a substrate having an insulating surface;
- a plurality of first lines extending in a first direction over said substrate;
- a plurality of second lines extending across said first lines over said substrate;
- a plurality of pixels defined by said first lines and said second lines;
 - a plurality of pixel electrodes provided at said pixels;
- a plurality of switching elements provided at said pixels, each of said switching elements comprising at least one first thin film transistor;
- an interlayer insulating film comprising resin formed over said plurality of switching elements wherein said pixel electrodes are provided over said interlayer insulating film;

a driver circuit formed over said substrate and

electrically connected to said plurality of first lines, said driver circuit comprising a plurality of second thin film transistors,

- 8. The display device according to claim 7 wherein said display device is a liquid crystal device.
- 9. The display device according to claim 7 further comprising another driver circuit comprising IC chips electrically connected to said plurality of second lines.
- 10. The display device according to claim 7 wherein said first thin film transistor has a channel region comprising crystalline silicon and a concentration of oxygen in said channel region is not higher than $7x10^{19}$ atoms/cm³.
 - 11. A display device comprising:
 - a substrate having an insulating surface;
- a plurality of first lines extending in a first direction over said substrate;
- a plurality of second lines extending across said first lines over said substrate;
- a plurality of pixels defined by said first lines and said second lines;
 - a plurality of pixel electrodes provided at said pixels;
- a plurality of switching elements provided at said pixels, each of said switching elements comprising at least one first thin film transistor;
 - a driver circuit formed over said substrate and

electrically connected to said plurality of first lines, said driver circuit comprising a plurality of second thin film transistors, each of said first and second thin film transistors comprising:

a semiconductor film formed over said substrate having at least source, drain and channel regions wherein said semiconductor film contains oxygen at a concentration not higher than $7x10^{19}$ atoms/cm³;

- a gate insulating film adjacent said semiconductor film; and
- a gate electrode adjacent said channel region with the gate insulating film interposed therebetween,

- 12. The display device according to claim 11 wherein said display device is a liquid crystal device.
- 13. The display device according to claim 11 further comprising another driver circuit comprising IC chips electrically connected to said plurality of second lines.
- 14. The display device according to claim 11 wherein said gate electrode is located over said channel region.
 - 15. A display device comprising:
 - a substrate having an insulating surface;
- a plurality of first lines extending in a first direction over said substrate;
- a plurality of second lines extending across said first lines over said substrate;
- a plurality of pixels defined by said first lines and said second lines;
 - a plurality of pixel electrodes provided at said pixels;

a plurality of switching elements provided at said pixels, each of said switching elements comprising at least one first thin film transistor;

an interlayer insulating film comprising resin formed over said plurality of switching elements wherein said pixel electrodes are provided over said interlayer insulating film;

a driver circuit formed over said substrate and electrically connected to said plurality of first lines, said driver circuit comprising a plurality of second thin film transistors, each of said first and second thin film transistors comprising:

a semiconductor film comprising silicon formed over said substrate having at least source, drain and channel regions;

a gate insulating film formed on said semiconductor film; and

a gate electrode over said channel region with the gate insulating film interposed therebetween,

- 16. The display device according to claim 15 wherein said display device is a liquid crystal device.
- 17. The display device according to claim 15 further comprising another driver circuit comprising IC chips electrically connected to said plurality of second lines.
- 18. The display device according to claim 15 wherein said semiconductor film contains oxygen at a concentration not higher than $7x10^{19}$ atoms/cm³.
 - 19. A display device comprising:
 - a substrate having an insulating surface;
 - a plurality of pixel electrodes formed over said substrate;

a plurality of first n-channel thin film transistors for switching said pixel electrodes;

a driver circuit formed over said substrate for switching said first thin film transistors, said driver circuit comprising a plurality of said second thin film transistors,

wherein all of said second thin film transistors are p-channel thin film transistors.

- 20. The display device according to claim 19 wherein said display device is a liquid crystal device.
- 21. The display device according to claim 19 further comprising another driver circuit comprising IC chips for driving said first thin film transistors.

22. A display device comprising:

- a substrate having an insulating surface;
- a plurality of first lines extending in a first direction over said substrate;
- a plurality of second lines extending across said first lines over said substrate;
- a plurality of pixels defined by said first lines and said second lines;
 - a plurality of pixel electrodes provided at said pixels;
- a plurality of switching elements provided at said pixels, each of said switching elements comprising at least one first thin film transistor;
- a driver circuit formed over said substrate and electrically connected to said plurality of first lines, said driver circuit comprising a plurality of second thin film transistors, each of said first and second thin film transistors comprising:
- a semiconductor film formed over said substrate having at least source, drain and channel regions;

a gate insulating film formed on said semiconductor film; and

a gate electrode over said channel region with the gate insulating film interposed therebetween,

- 23. The display device according to claim 22 wherein said display device is a liquid crystal device.
- 24. The display device according to claim 22 further comprising another driver circuit comprising IC chips electrically connected to said plurality of second lines.
- 25. The display device according to claim 22 wherein said semiconductor film contains oxygen at a concentration not higher than $7x10^{19}$ atoms/cm³.
 - 26. A display device comprising:
 - a substrate having an insulating surface;
- a plurality of first lines extending in a first direction over said substrate;
- a plurality of second lines extending across said first lines over said substrate;
- a plurality of pixels defined by said first lines and said second lines:
 - a plurality of pixel electrodes provided at said pixels;
- a plurality of switching elements provided at said pixels, each of said switching elements comprising at least one first thin film transistor;
- an interlayer insulating film comprising resin formed over said plurality of switching elements wherein said pixel electrodes are provided over said interlayer insulating film;

a driver circuit formed over said substrate and electrically connected to said plurality of first lines, said driver circuit comprising a plurality of second thin film transistors,

- 27. The display device according to claim 26 wherein said display device is a liquid crystal device.
- 28. The display device according to claim 26 further comprising another driver circuit comprising IC chips electrically connected to said plurality of second lines.
- 29. The display device according to claim 26 all of the first thin film transistors and the second thin film transistors are top-gate type.
- 30. The display device according to claim 26 wherein said first thin film transistor has a channel region comprising crystalline silicon having an oxygen concentration not higher than $7x10^{19}$ atoms/cm³.